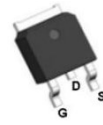


650V 2A 3.8Ω N-ch Power MOSFET

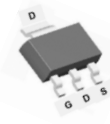
Description

DT2 MOS is DIN-TEK 2nd generation VDMOS family that is dramatic reduction in on-resistance and ultra-low gate charge for applications requiring high power density and high efficiency. And it is very robust and RoHS compliant.

TO-252



SOT-223-3L



TO-220F

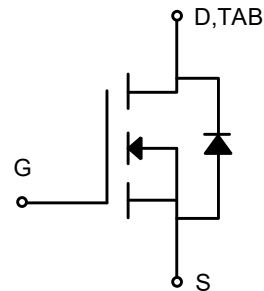


Features

- Typ. $R_{DS(on)}=3.8\Omega@V_{GS}=10V$
- 100% avalanche tested
- RoHS Compliant

Applications

- SMPS
- Charger
- DC-DC



Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	DTU2N65	DTB2N65	DTP2N65F	Unit
Drain-source voltage	V_{DSS}		650		V
Gate-source voltage	V_{GS}		± 30		V
Continuous drain current	I_D		2		A
Pulsed drain current ¹	I_{DM}		8		A
Avalanche energy, single pulse ²	E_{AS}		20		mJ
Power dissipation	P_D	26	-	20	W
Derate above 25°C		0.2	-	0.2	W/°C
Operating junction temperature	T_j		-55~150		°C
Storage temperature	T_{stg}		-55~150		°C
Continuous diode forward current	I_S		2		A
Diode pulse current	I_{Spulse}		8		A
Thermal resistance, junction-to-case	$R_{\theta JC}$	4.78	-	6.25	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	110	-	62.5	°C/W

Electrical Characteristics of MOSFET

Parameter	Symbol	Test Condition		Min.	Typ.	Max.	Unit
Drain-source break down voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	$T_C=25^\circ C$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	$T_J=25^\circ C$	2.0	-	4.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$	$T_J=25^\circ C$	-	-	1	μA
		$V_{DS}=520V, V_{GS}=0V$	$T_J=125^\circ C$	-	-	100	μA
Gate-source leakage current,forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	$T_J=25^\circ C$	-	-	100	nA
Gate-source leakage current,reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	$T_J=25^\circ C$	-	-	-100	nA
Drain-source on-state resistance ³	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	$T_J=25^\circ C$	-	3.8	5	Ω
Transconductance ³	G_{fs}	$V_{DS}=20V$	$T_J=25^\circ C$	-	5.7	-	S

Dynamic Characteristics of MOSFET ($T_C=25^\circ C$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V, V_{GS}=0V$	-	320	-	pF
Output capacitance	C_{oss}		-	27	-	pF
Reverse transfer capacitance	C_{rss}		-	2	-	pF
Gate to source charge	Q_{gs}	$V_{DD}=190V$	-	2	-	nC
Gate to drain charge	Q_{gd}	$I_D=2A$	-	2	-	nC
Total gate charge	Q_g	$V_{GS}=0$ to 10V	-	7	-	nC

Switching Characteristics of MOSFET ($T_C=25^\circ C$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Turn-on delay time	$t_{d on}$	$V_{DS}=320V, I_D=2A,$ $R_G=25\Omega, V_{GS}=0$ to 10V	-	7	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d off}$		-	35	-	ns
Fall time	t_f		-	20	-	ns

Characteristics of Body Diode ($T_C=25^\circ C$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage	V_{SD}	$I_{SD}=2A, V_{GS}=0V$	-	-	1.4	V
Reverse recovery time	t_{rr}	$V_{DS}=320V, I_S=2A, V_{GS}=0V$ $di/dt=100A/\mu s$	-	180	-	ns
Reverse recovery current	I_{rr}		-	8	-	A
Recovery charge	Q_{rr}		-	0.7	-	μC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$.
2. The E_{AS} data shows Max. rating . The test condition is $V_{DD}=50V, V_{GS}=10V, L=10mH, I_{AS}=2A, T_C=25^\circ C$.
3. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

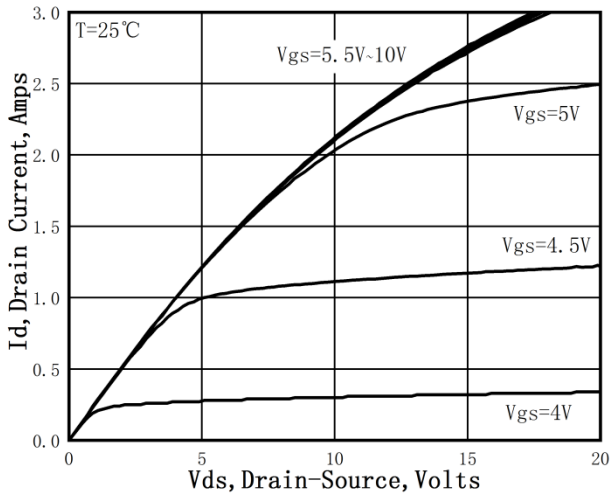


Figure 1. On-Region Characteristics

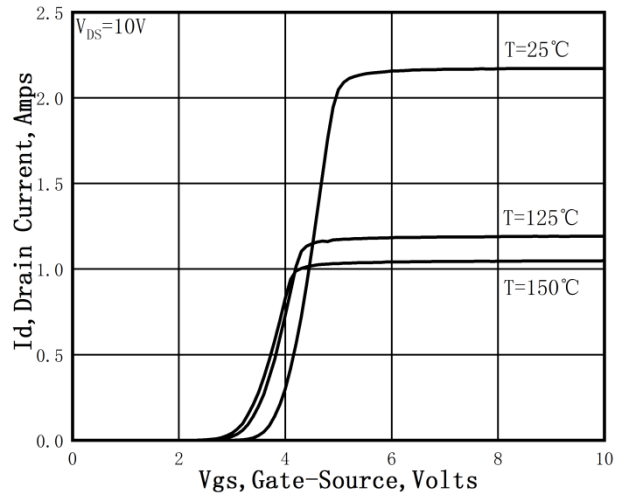


Figure 2. Transfer Characteristics

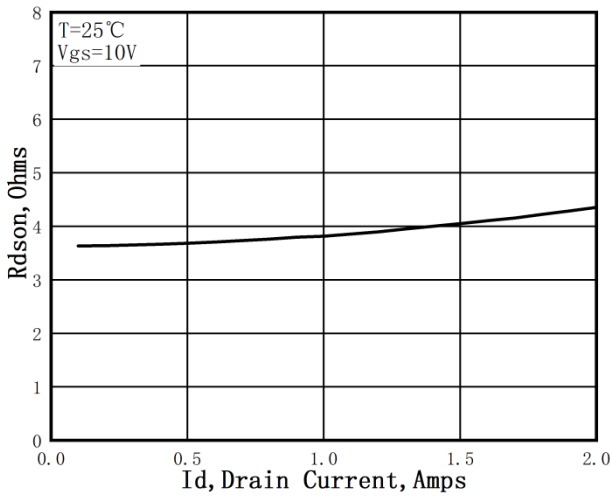


Figure 3. Static Drain-Source On Resistance

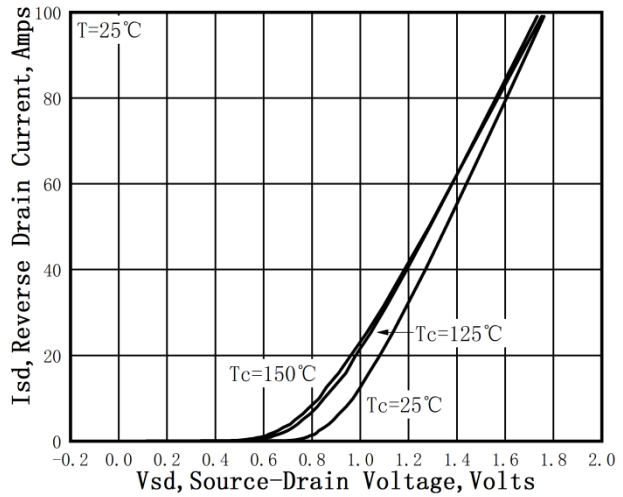


Figure 4. Typical Body Diode Transfer Characteristics

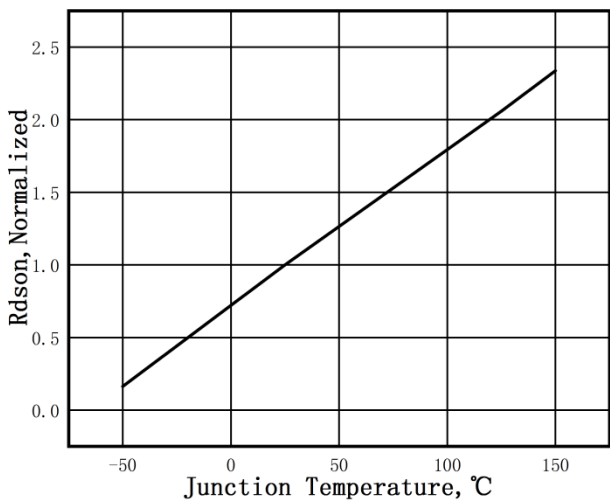


Figure 5. Normalized $R_{DS(on)}$ vs. Temperature

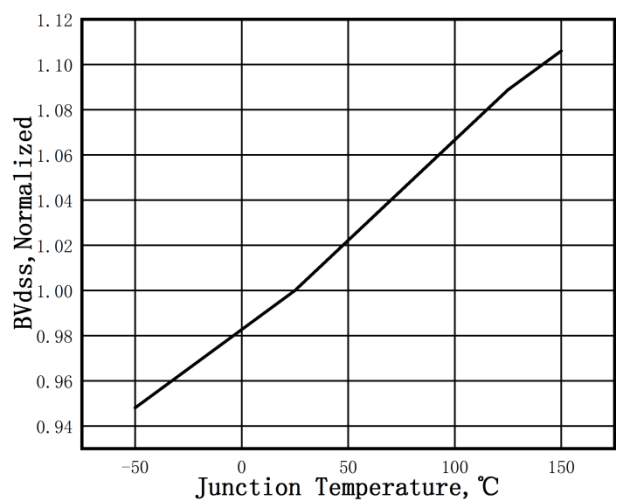


Figure 6. Normalized BV_{DS} vs. Temperature

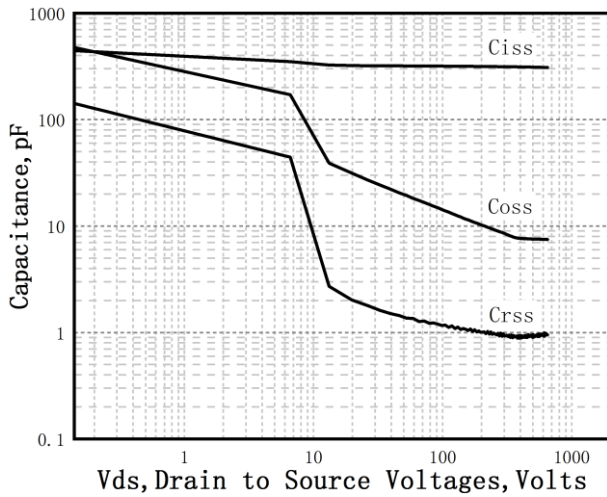


Figure 7. Capacitance Characteristics

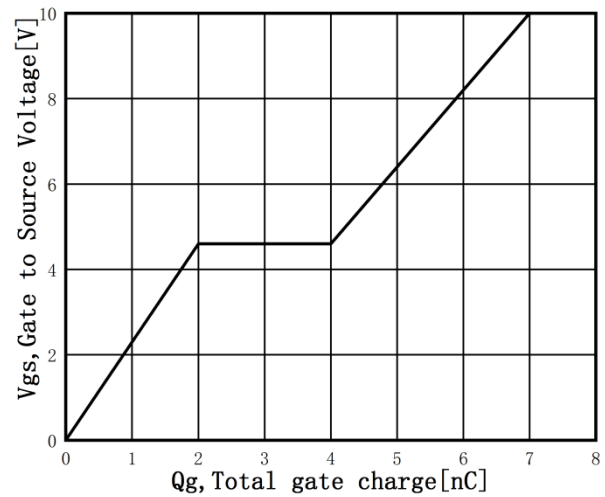


Figure 8. Gate Charge Characteristics

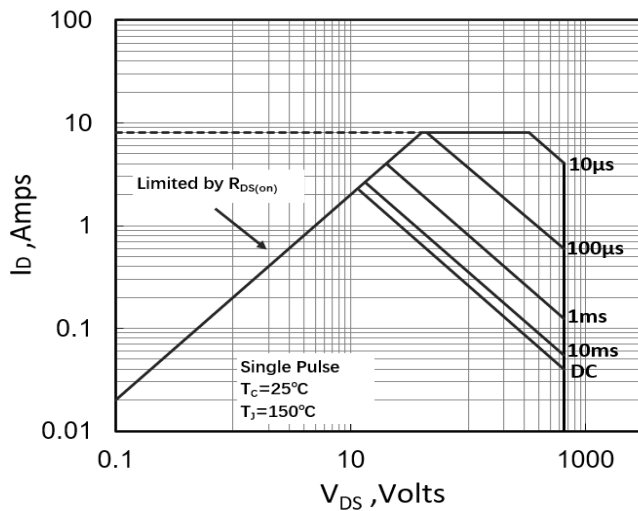


Figure 9. Maximum Safe Operating Area (TO-252)

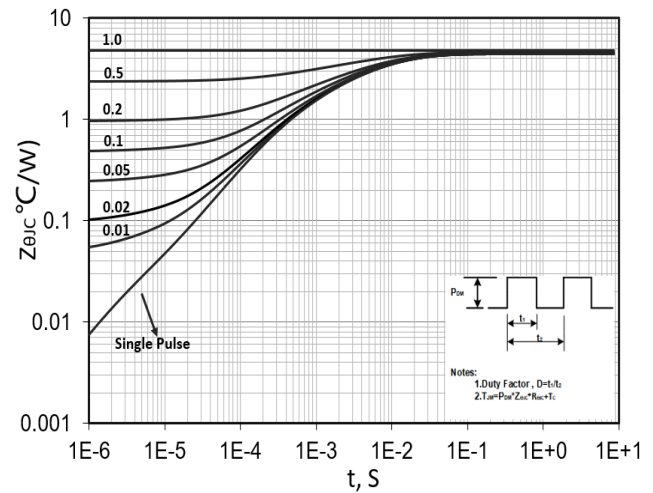


Figure 10. Transient Thermal Response Curve (TO-252)

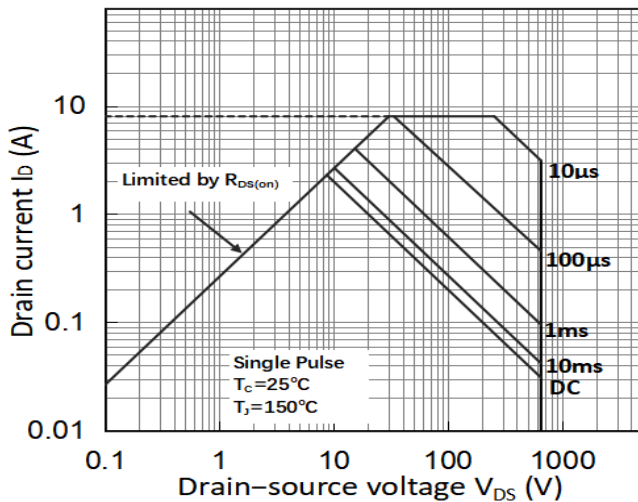


Figure 11. Maximum Safe Operating Area (TO-220F)

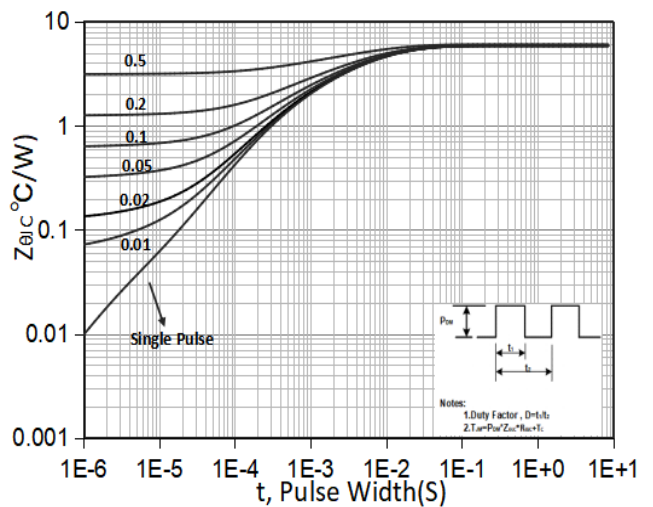
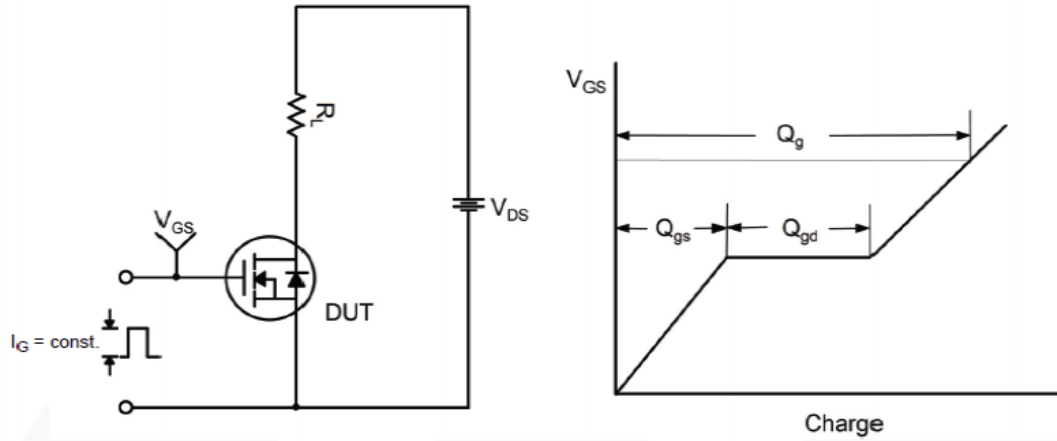
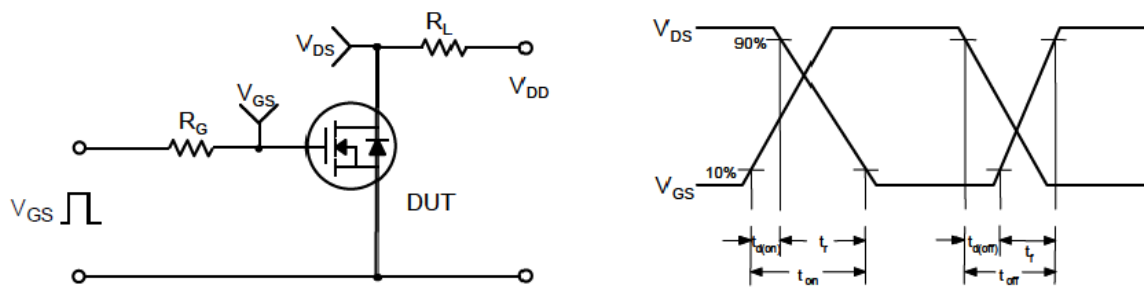


Figure 12. Transient Thermal Response Curve (TO-220F)

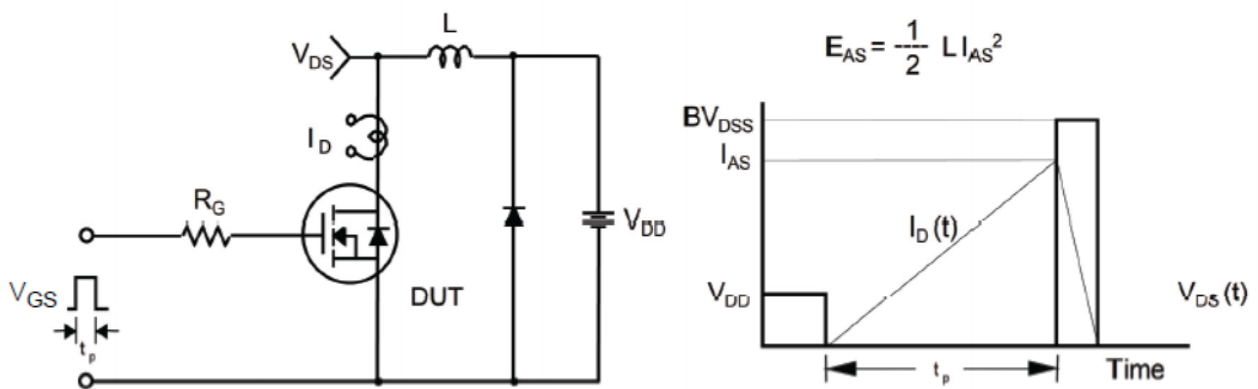
Gate Charge Test Circuit & Waveform



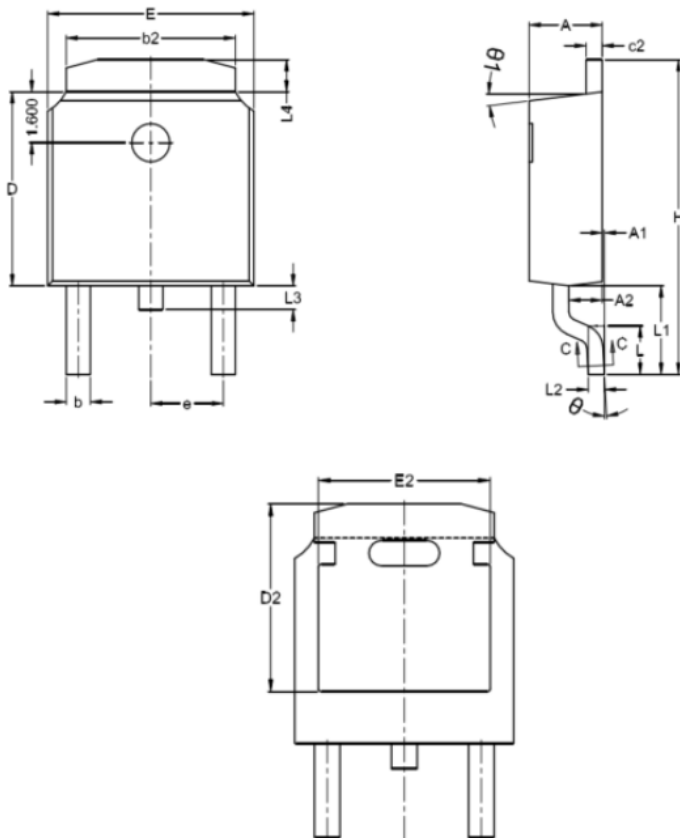
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



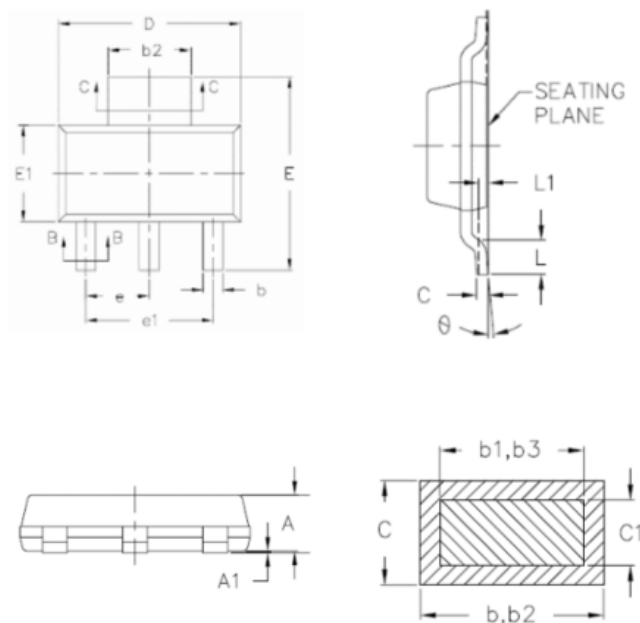
Mechanical Dimensions for TO-252



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	2.10	2.50
A1	0	0.15
b	0.7	0.9
b2	5.13	5.54
c	0.44	0.65
c2	0.45	0.65
D	6.00	6.20
D2	5.37	5.78
E	6.30	6.90
E2	4.90	5.30
e	2.23	2.33
H	9.7	10.5
L	1.38	1.73
L1	2.58	3.00
L2	0.50	0.52
L3	0.60	1.00
L4	0.81	1.42

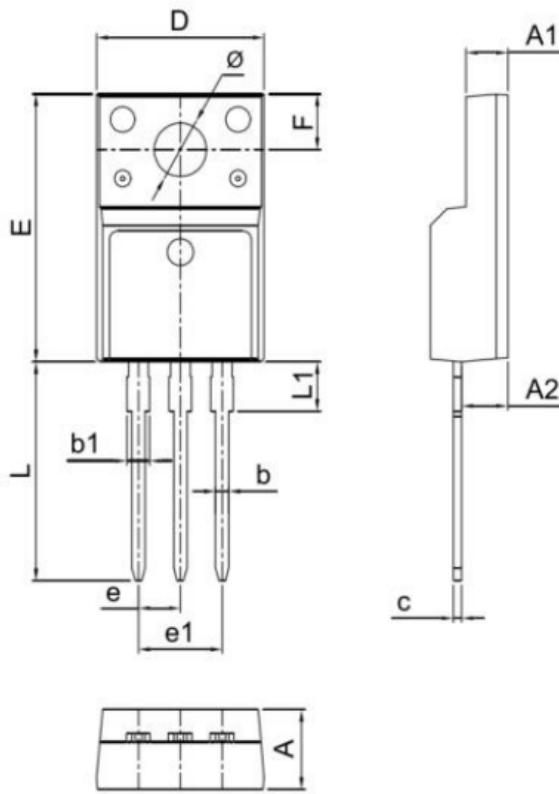
Mechanical Dimensions for SOT-223-3L



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	-	1.80
A1	0.02	0.10
b	0.66	0.84
b1	0.60	0.79
b2	2.90	3.10
b3	2.84	3.05
c	0.23	0.35
c1	0.23	0.33
D	6.20	6.70
E	6.70	7.30
E1	3.30	3.70
e	2.30BSC	
e1	4.60BSC	
L	0.80	-
L1	0.25BSC	
theta	0°	10°

Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.5	5
A1	2.34	2.8
A2	2.6	3.05
b	0.7	0.94
b1	1.14	1.58
c	0.4	0.64
D	9.95	10.36
E	15.4	16.07
e	2.44	2.64
e1	4.88	5.26
F	2.95	3.55
L	12.64	13.5
L1	2.8	3.8
A	4.5	4.9
Φ	3.08	3.3

Ordering Information

Part	Package	Marking	Packing method	Minimum packing number
DTU2N65	TO-252	DTU2N65	Tape and reel	2.5K / Reel
DTB2N65	SOT-223-3L	DTB2N65	Tape and reel	2.5K / Reel
DTP2N65F	TO-220F	DTP2N65F	Tube	50 / Tube

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